

Docket No. 247627US2SRD DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yoshiaki SAITO, et al.

SERIAL NO: New Divisional Application

GAU:

FILED: Herewith

EXAMINER:

FOR: MAGNETIC MEMORY

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449 which were submitted in Application Serial no. 09/912,321 filed 07/26/01 and Application Serial No. 10/357,217 filed 02/04/03, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

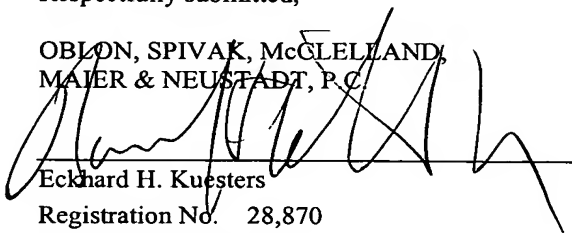
- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.


Eckhard H. Kuesters

Registration No. 28,870
Attorney of Record

Customer Number

22850

Tel. (703) 413-3000
Fax. (703) 413-2220
(OSMMN 05/03)

Raymond F. Cardillo, Jr.
Registration No. 40,440

Form PTO 1449 U.S. DEPARTMENT OF
COMMERCE
(Modified) PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.
247627US-2SRD DIV

APPLN. SERIAL NO.
New Div. Appln.

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

YOSHIAKI SAITO, ET AL.

FILED

HEREWITH

GROUP

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIAT E
	AA	5,659,499	08/19/97	E. Chen, et al.			
	AB	5,956,267	09/21/99	A. T. Hurst, et al.			
	AC	5,940,319	08/17/99	M. Durlam, et al.			
	AD	6,178,074	01/2001	Gill			
	AE	6,233,172	05/2001	Chen et al.			
	AF	5,173,873	12/1992	Wu et al.			
	AC	5,757,056	05/1998	Chui			
	AH	6,054,734	04/2000	Aozana et al.			
	AI	6,205,052	03/2001	Slaughter et al.			
	AJ	6,556,473	04/2003	Saito et al.			
	AK	5,768,181	06/1998	Zhu et al.			
	AL	5,838,608	11/1998	Zhu et al.			
	AM	6,072,718	06/2000	Abraham et al.			
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO	
	AO	WO 00/10172	02/24/00	WIPO (with English abstract)		x
	AP	10-4227	01/06/98	Japan		x
	AQ					
	AP					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	J.S. MOODERA, et al., J. Appl. Phys., Vol. 79, No. 8, pps. 4724-4729, "FERROMAGNETIC-INSULATOR-FERROMAGNETIC TUNNELING: SPIN-DEPENDENT TUNNELING AND LARGE MAGNETORESISTANCE IN TRILAYER JUNCTIONS (INVITED)," April 15, 1996
	AX	L.F. SCHELP, et al., Physical Review B, Vol. 56, No. 10, pps. R5747 - R5750, "SPIN-DEPENDENT TUNNELING WITH COULOMB BLOCKADE," September 1, 1997
	AY	Y. SAITO, et al., J. Magnetic. Soc., Vol. 23, No. 4-2, pps. 1269-1272, "SPIN-DEPENDENT TUNNELING THROUGH LAYERED HARD-MAGNETIC NANO-PARTICLES," 1999
	AZ	F. MONTAIGNE, et al., Applied Physics Letters, Vol. 73, No. 19, pps. 2829-2831, "ENHANCED TUNNEL MAGNETORESISTANCE AT HIGH BIAS VOLTAGE IN DOUBLE-BARRIER PLANAR JUNCTIONS," November 9, 1998

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.